L Number	Hits	Search Text	DB	Time stamp
17	473	(polysilicon with (doped) with (undoped)) SAME gate	USPAT; US-PGPUB	2002/11/03 16:52
22	417	((polysilicon with (doped) with (undoped)) SAME gate) and transistor	USPAT; US-PGPUB	2002/11/03 16:52
23	302	(((polysilicon with (doped) with (undoped)) SAME gate) and transistor) and 438/$.ccls.	USPAT; US-PGPUB	2002/11/03 17:02
24	0	20010026962.URPN.	USPAT	2002/11/03 16:53
25	25	(gate WITH stack) with (doped) with undoped	USPAT; US-PGPUB	2002/11/03 17:02
-	125	("oxide nitride oxide" or ono or "oxide/nitride/oxide") same (nitridation or nitridating or nitriding or nitrided or nitrification or nitricate or nitridate)	USPAT; US-PGPUB	2002/10/23 15:55
-	68	(("oxide nitride oxide" or ono or "oxide/nitride/oxide") same (nitridation or nitridating or nitriding or nitrided or nitrification or nitricate or nitridate)) and (oxidizes or oxidize or oxidizing or oxidized)	USPAT; US-PGPUB	2002/10/23 11:16
-	68	((("oxide nitride oxide" or ono or "oxide/nitride/oxide") same (nitridation or nitridating or nitriding or nitrided or nitrification or nitricate or nitridate)) and (oxidizes or oxidize or oxidizing or oxidized)) and ("N.sub.2O" or "N.sub.2 O" or "N2O" or "NO")	USPAT; US-PGPUB	2002/10/23 11:19
-	1	("6,246,076").PN.	USPAT; US-PGPUB	2002/10/23 11:42
-	15	("3560810" | "4003071" | "4621277" | "4748131" | "4851370" | "5034798" | "5061647" | "5258333" | "5286994" | "5294820" | "5364803" | "5382533" | "5429995" | "5462812" | "5552332").PN.	USPAT	2002/10/23 12:43
-	27	5552332.URPN.	USPAT	2002/10/23 12:46
-	9	("5296411" | "5403786" | "5464792" | "5605848" | "5650344" | "5661072" | "5672521" | "5851892" | "6001694").PN.	USPAT	2002/10/23 13:20
-	41	(nitrogen) WITH (diffuse or diffusing or diffused) WITH oxide WITH (anneal or annealing or heating)	USPAT; US-PGPUB	2002/10/23 13:55
-	107	(oxynitride or "oxy nitride" or SiON) SAME (nitridating or "N.sub.2O" or "N.sub.2 O" or N2O or "nitrous oxide") SAME (oxidizing or oxidizes or oxidized or oxidating)	USPAT; US-PGPUB	2002/10/23 14:07
-	235	(oxynitride or "oxy nitride" or SiON) and ((oxide or dioxide) SAME(nitridating or "N.sub.2O" or "N.sub.2 O" or N2O or "nitrous oxide") SAME (oxidizing or oxidizes or oxidized or oxidating))	USPAT; US-PGPUB	2002/10/23 14:02
-	99	(oxynitride or "oxy nitride" or SiON) SAME (nitridating or nitridation or nitriding or nitrided or nitrification or nitricate or nitridate or nitrified or nitrify or nitrifies) SAME (oxidizing or oxidizes or oxidized or oxidating)	USPAT; US-PGPUB	2002/10/23 14:27
-	38278	oxide with nitrogen	USPAT; US-PGPUB	2002/10/23 14:23
-	239	(("oxide nitride" or "nitride oxide") SAME (nitridating or nitridation or nitriding or nitrided or nitrification or nitricate or nitridate or nitrified or nitrify or nitrifies)) and (oxidizing or oxidizes or oxidized or oxidating)	USPAT; US-PGPUB	2002/10/23 15:06
-	1	("4,623,912").PN.	USPAT; US-PGPUB	2002/10/23 15:06

-		222	((("oxide nitride" or "nitride oxide") SAME (nitridating or nitridation or nitriding or nitrided or nitrification or nitricate or nitridate or nitrified or nitrify or nitrifies)) and (oxidizing or oxidizes or oxidized or oxidating)) not ((oxynitride or "oxy nitride" or SiON) SAME (nitridating or nitridation or nitriding or nitrided or nitrification or nitricate or nitridate or nitrified or nitrify or nitrifies) SAME (oxidizing or oxidizes or oxidized or oxidating))	USPAT; US-PGPUB	2002/10/23 15:43
-		270	(438/261).CCLS.	USPAT; US-PGPUB	2002/10/23 15:40
-		28	(((("oxide nitride" or "nitride oxide") SAME (nitridating or nitridation or nitriding or nitrided or nitrification or nitricate or nitridate or nitrified or nitrify or nitrifies)) and (oxidizing or oxidizes or oxidized or oxidating)) not ((oxynitride or "oxy nitride" or SiON) SAME (nitridating or nitridation or nitriding or nitrided or nitrification or nitricate or nitridate or nitrified or nitrify or nitrifies) SAME (oxidizing or oxidizes or oxidized or oxidating))) and (EPROM or "floating gate" or EEPROM)	USPAT; US-PGPUB	2002/10/23 15:44
-		126	(oxide with nitrogen) and ("oxide nitride oxide" or ono or "oxide/nitride/oxide") and (nitridation or nitridating or nitriding or nitrided or nitrification or nitricate or nitridate) and (((anneal or annealing) with (oxygen or "O.sub.2")) or (oxidizing or oxidation or oxidizes))	USPAT; US-PGPUB	2002/10/23 15:57
-		1	("5,296,411").PN.	USPAT; US-PGPUB	2002/10/24 11:08
-		5	("4567061" | "4784975" | "5296411" | "5306658" | "5382550").PN.	USPAT	2002/10/24 11:16
-		35	5296411.URPN.	USPAT	2002/10/24 11:20
-		18	5726087.URPN.	USPAT	2002/10/24 11:46
-		8	("4360900" | "5060034" | "5304829" | "5371028" | "5536667" | "5619051" | "5661056" | "5888870").PN.	USPAT	2002/10/24 12:50
-		506	(interpoly or interpolysilicon or interlayer) with (ONO or "oxide nitride oxide")	USPAT; US-PGPUB	2002/10/24 16:43
-		476	((interpoly or interpolysilicon or interlayer) with (ONO or "oxide nitride oxide")) and (EPROM or "floating gate")	USPAT; US-PGPUB	2002/10/24 16:15
-		4	(((interpoly or interpolysilicon or interlayer) with (ONO or "oxide nitride oxide")) and (EPROM or "floating gate")) and ((oxide or dioxdie) with (dichlorosilane or "di chlorosilane" or "dicholor silane" or DCS) with ("nitrous oxide" or "nitric oxide" or "N.sub.2 O" or "N.sub.20"))	USPAT; US-PGPUB	2002/10/24 16:37
-		5	("5208174" | "5219774" | "5619052" | "5677867" | "5726087").PN.	USPAT	2002/10/24 16:27
-		0	(((interpoly or interpolysilicon or interlayer) with (ONO or "oxide nitride oxide")) and (EPROM or "floating gate")) and ((oxide or dioxdie) with ("SiH.sub.2 Cl.sub.2") with ("nitrous oxide" or "nitric oxide" or "N.sub.2 O" or "N.sub.20"))	USPAT; US-PGPUB	2002/10/24 16:38

-	0	(((interpoly or interpolysilicon or interlayer) with (ONO or "oxide nitride oxide")) and (EPROM or "floating gate")) and ((oxide or dioxide) with ("SiH.sub.2 Cl.sub.2") with ("nitrous oxide" or "nitric oxide" or "N.sub.2 O" or "N.sub.20"))	USPAT; US-PGPUB	2002/10/24 16:39
-	14	(((interpoly or interpolysilicon or interlayer) with (ONO or "oxide nitride oxide")) and (EPROM or "floating gate")) and ((oxide or dioxide) Same ("SiH.sub.2 Cl.sub.2") same ("nitrous oxide" or "nitric oxide" or "N.sub.2 O" or "N.sub.20"))	USPAT; US-PGPUB	2002/10/24 16:42
-	10	("control gate" with doped with undoped) and (EPROM or "EEPROM")	USPAT; US-PGPUB	2002/10/24 18:01
-	29	(gate with doped with undoped) and (EPROM or "EEPROM") and (ONO or oxynitride)	USPAT; US-PGPUB	2002/10/24 17:13
-	27	((gate with doped with undoped) and (EPROM or "EEPROM") and (ONO or oxynitride)) not (("control gate" with doped with undoped) and (EPROM or "EEPROM"))	USPAT; US-PGPUB	2002/10/24 16:58
-	1	("5272099").PN.	USPAT; US-PGPUB	2002/10/24 17:09
-	11	("control gate" SAME (doped with undoped)) and (EPROM or EEPROM) and (ONO or oxynitride)	USPAT; US-PGPUB	2002/10/24 17:16
-	8	("control gate" SAME (doped with undoped)) and ("flash memory") and (ONO or oxynitride)	USPAT; US-PGPUB	2002/10/24 17:20
-	14	("control gate" SAME (doped with undoped)) and ("flash memory")	USPAT; US-PGPUB	2002/10/24 17:20
-	6	(("control gate" SAME (doped with undoped)) and ("flash memory")) not (("control gate" SAME (doped with undoped)) and ("flash memory") and (ONO or oxynitride))	USPAT; US-PGPUB	2002/10/24 17:21
-	37	("control gate" SAME (doped with undoped)) and (EPROM or "EEPROM")	USPAT; US-PGPUB	2002/10/24 17:43
-	10	("control gate" and (doped with undoped)) and 438/261.ccls.	USPAT; US-PGPUB	2002/10/24 17:47
-	64	("control gate" SAME (doped with undoped))	USPAT; US-PGPUB	2002/10/24 17:49
-	15	("control gate" with (doped with undoped))	USPAT; US-PGPUB	2002/10/24 18:08
-	49	(("control gate" SAME (doped with undoped))) not (("control gate" with (doped with undoped)))	USPAT; US-PGPUB	2002/10/24 17:49
-	2801	("control gate" with (polysilicon))	USPAT; US-PGPUB	2002/10/24 18:09
-	1352	(("control gate" with (polysilicon))) and eprom	USPAT; US-PGPUB	2002/10/24 18:09
-	86	(polysilicon with (doped) with (undoped)) and "control gate"	USPAT; US-PGPUB	2002/10/24 18:17
-	33	(polysilicon with (doped) with (undoped)) and EPROM	USPAT; US-PGPUB	2002/11/03 16:50
-	2665	(("in situ" or insitu or "in-situ") WITH (polysilicon or poly or silicon))	USPAT; US-PGPUB	2002/10/24 18:24
-	160	((("in situ" or insitu or "in-situ") WITH (polysilicon or poly or silicon))) SAME (doped with undoped)	USPAT; US-PGPUB	2002/10/24 18:25
-	13	(((("in situ" or insitu or "in-situ") WITH (polysilicon or poly or silicon))) SAME (doped with undoped)) and (eprom or eeprom)	USPAT; US-PGPUB	2002/10/24 18:43
-	1	("6281078").PN.	USPAT; US-PGPUB	2002/10/24 18:46
-	627	(silane or "SiH.sub.4" or phosphene "PH.sub.3") same (polysilicon or silicon or poly) same undoped	USPAT; US-PGPUB	2002/10/24 18:47

–	254	((silane or "SiH.sub.4" or phosphene "PH.sub.3") same (polysilicon or silicon or poly) same undoped) and memory	USPAT; US-PGPUB	2002/10/24 18:47
–	58	(((silane or "SiH.sub.4" or phosphene "PH.sub.3") same (polysilicon or silicon or poly) same undoped) and memory) and (ono or "oxide nitride oxide")	USPAT; US-PGPUB	2002/10/24 19:00